

DATA SHEET

NEC

SILICON POWER MOS FET NE5500479A

3.5 V OPERATION SILICON RF POWER LDMOS FET FOR 900 MHz 1 W TRANSMISSION AMPLIFIERS

DESCRIPTION

The NE5500479A is an N-channel silicon power MOS FET specially designed as the transmission power amplifier for cellular handsets. Dies are manufactured using our NEWMOS technology (our 0.6 μm WSi gate laterally diffused MOS FET) and housed in a surface mount package. The device can deliver 31.5 dBm output power with 62% power added efficiency at 900 MHz as AMPS final output stage amplifier under the 3.5 V supply voltage. It also can deliver 35 dBm output power with 62% power added efficiency at 4.8 V, as GSM 900 class 4 final stage amplifiers.

FEATURES

- High output power : $P_{\text{out}} = 31.5 \text{ dBm TYP.}$ ($V_{\text{DS}} = 3.5 \text{ V}$, $I_{\text{Dset}} = 300 \text{ mA}$, $f = 900 \text{ MHz}$, $P_{\text{in}} = 20 \text{ dBm}$)
- High power added efficiency : $\eta_{\text{add}} = 62\% \text{ TYP.}$ ($V_{\text{DS}} = 3.5 \text{ V}$, $I_{\text{Dset}} = 300 \text{ mA}$, $f = 900 \text{ MHz}$, $P_{\text{in}} = 20 \text{ dBm}$)
- High linear gain : $G_{\text{L}} = 15.0 \text{ dB TYP.}$ ($V_{\text{DS}} = 3.5 \text{ V}$, $I_{\text{Dset}} = 300 \text{ mA}$, $f = 900 \text{ MHz}$, $P_{\text{in}} = 10 \text{ dBm}$)
- Surface mount package : $5.7 \times 5.7 \times 1.1 \text{ mm MAX.}$
- ★ Single supply : $V_{\text{DS}} = 3.0 \text{ to } 8.0 \text{ V}$

APPLICATIONS

- Analog cellular phones : 3.5 V AMPS handsets
- Digital cellular phones : 4.8 V GSM 900 class 4 handsets
- Others : General purpose amplifiers for 800 to 1 000 MHz TDMA applications

ORDERING INFORMATION

Part Number	Package	Marking	Supplying Form
NE5500479A-T1	79A	R4	<ul style="list-style-type: none">• 12 mm wide embossed taping• Gate pin face the perforation side of the tape• Qty 1 kpcs/reel

Remark To order evaluation samples, contact your nearby sales office.
Part number for sample order: NE5500479A

Caution Observe precautions when handling because these devices are sensitive to electrostatic discharge.

The information in this document is subject to change without notice. Before using this document, please confirm that this is the latest version.
Not all devices/types available in every country. Please check with local NEC Compound Semiconductor Devices representative for availability and additional information.

ABSOLUTE MAXIMUM RATINGS (T_A = +25°C)

Parameter	Symbol	Ratings	Unit
Drain to Source Voltage	V _{DS}	20.0	V
Gate to Source Voltage	V _{GS}	5.0	V
Drain Current	I _D	1.0	A
Drain Current (Pulse Test)	I _D ^{Note}	2.0	A
Total Power Dissipation	P _{tot}	10	W
Channel Temperature	T _{ch}	125	°C
Storage Temperature	T _{stg}	-65 to +125	°C

Note Duty Cycle ≤ 50%, T_{on} ≤ 1 s

RECOMMENDED OPERATING CONDITIONS

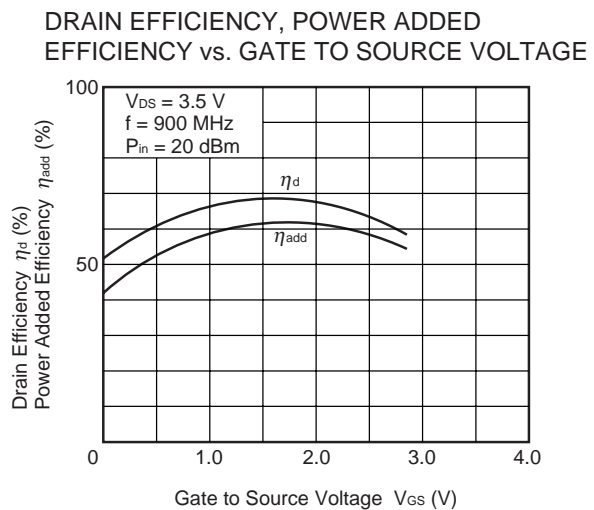
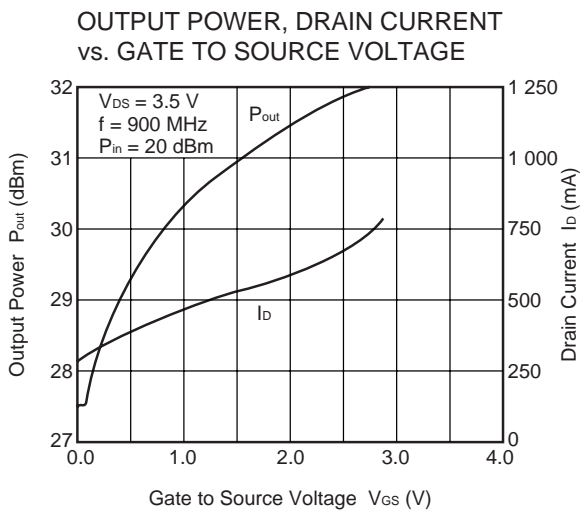
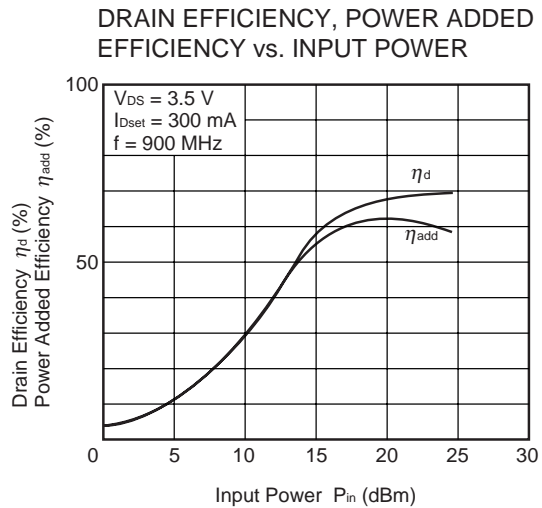
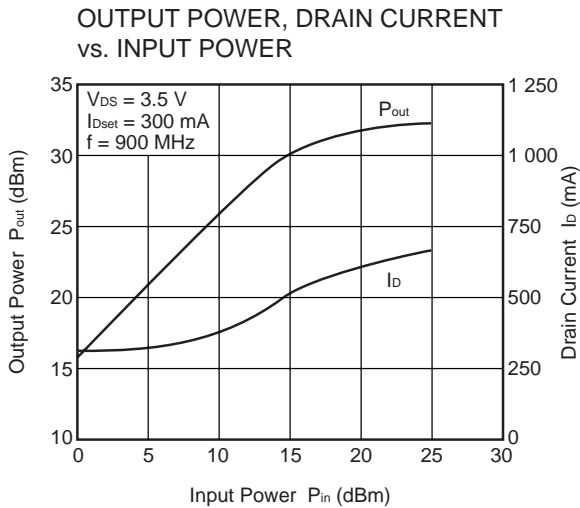
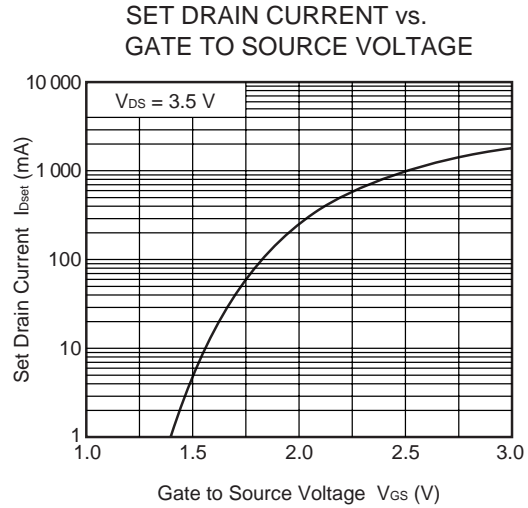
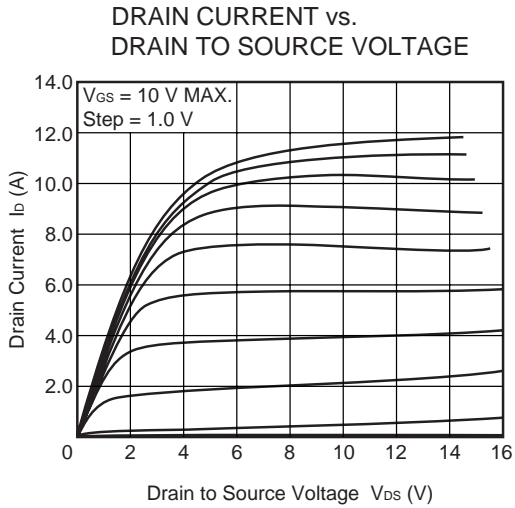
Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
★ Drain to Source Voltage	V _{DS}		3.0	3.5	8.0	V
Gate to Source Voltage	V _{GS}		0	2.0	3.5	V
Drain Current	I _D		-	600	700	mA
Input Power	P _{in}	f = 900 MHz, V _{DS} = 3.5 V	18	20	22	dBm

ELECTRICAL CHARACTERISTICS (T_A = +25°C)

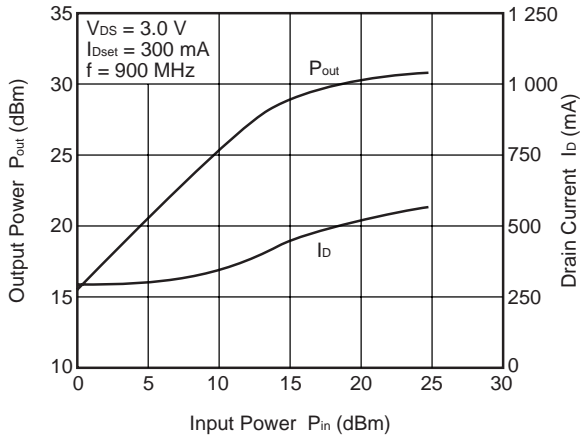
Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
Gate to Source Leak Current	I _{GSS}	V _{GSS} = 5.0 V	-	-	100	nA
Drain to Source Leakage Current (Zero Gate Voltage Drain Current)	I _{DSS}	V _{DSS} = 8.5 V	-	-	100	nA
Gate Threshold Voltage	V _{th}	V _{DS} = 4.8 V, I _D = 1 mA	1.0	1.35	2.0	V
Transconductance	G _m	V _{DS} = 4.8 V, I _D = 600 mA	-	1.43	-	S
Drain to Source Breakdown Voltage	BV _{DSS}	I _{DSS} = 10 μA	20	24	-	V
Thermal Resistance	R _{th}	Channel to Case	-	10	-	°C/W
Linear Gain	G _L	f = 900 MHz, P _{in} = 10 dBm, V _{DS} = 3.5 V, I _{Dset} = 300 mA, Note	-	15.0	-	dB
Output Power	P _{out}	f = 900 MHz, P _{in} = 20 dBm, V _{DS} = 3.5 V, I _{Dset} = 300 mA, Note	30.5	31.5	-	dBm
Operating Current	I _{op}		-	600	-	mA
Power Added Efficiency	η _{add}		55	62	-	%

Note DC performance is 100% testing. RF performance is testing several samples per wafer. Wafer rejection criteria for standard devices is 1 reject for several samples.

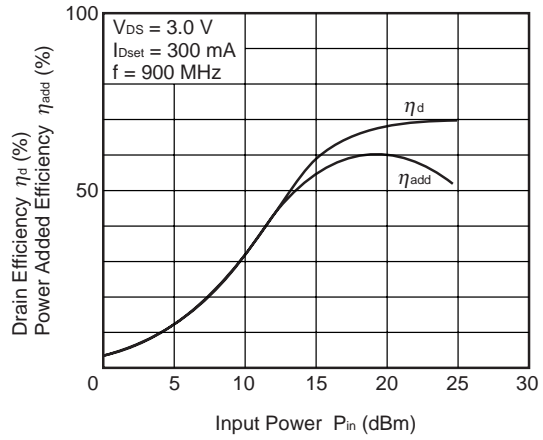
TYPICAL CHARACTERISTICS (T_A = +25°C)



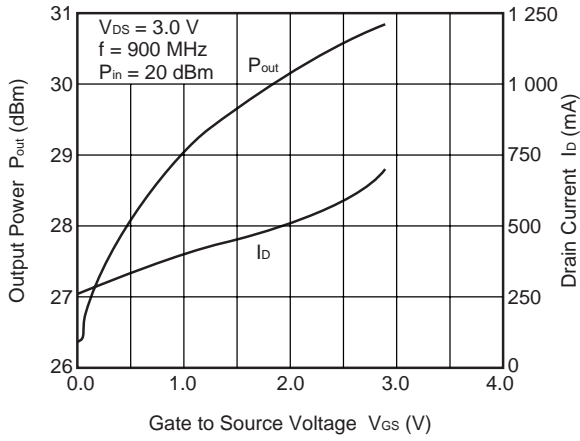
OUTPUT POWER, DRAIN CURRENT vs. INPUT POWER



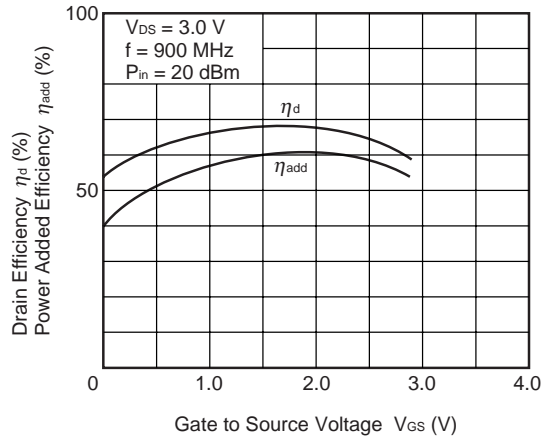
DRAIN EFFICIENCY, POWER ADDED EFFICIENCY vs. INPUT POWER



OUTPUT POWER, DRAIN CURRENT vs. GATE TO SOURCE VOLTAGE



DRAIN EFFICIENCY, POWER ADDED EFFICIENCY vs. GATE TO SOURCE VOLTAGE



Remark The graphs indicate nominal characteristics.

S-PARAMETERS

S-parameters/Noise parameters are provided on the NEC Compound Semiconductor Devices Web site in a form (S2P) that enables direct import to a microwave circuit simulator without keyboard input.

Click here to download S-parameters.

[RF and Microwave] → [Device Parameters]

URL <http://www.csd-nec.com/>

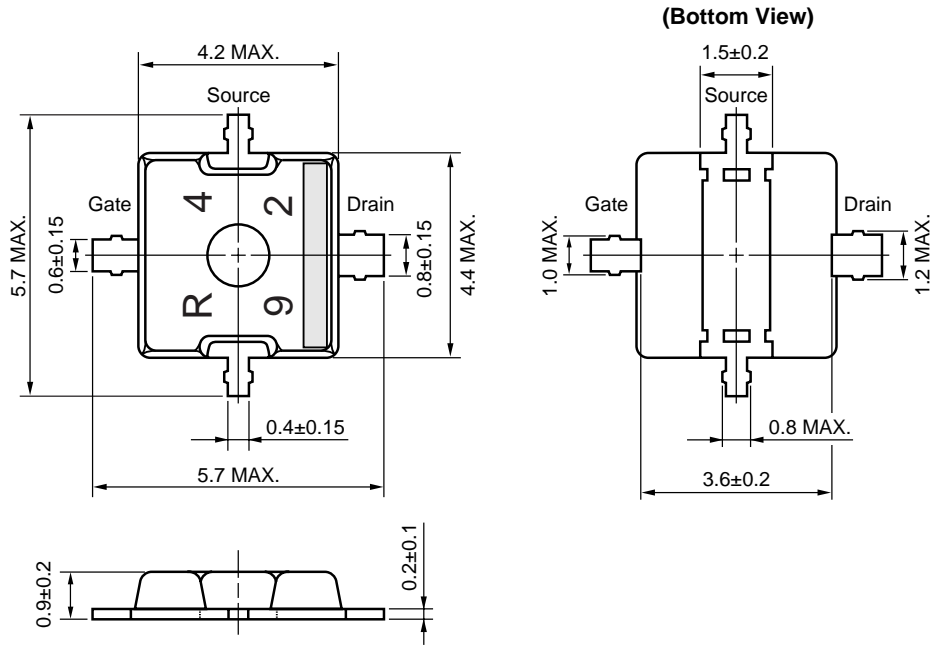
LARGE SIGNAL IMPEDANCE ($V_{DS} = 3.5 \text{ V}$, $I_D = 300 \text{ mA}$, $P_{in} = 20 \text{ dBm}$)

f (MHz)	Z_{in} (Ω)	Z_{OL} (Ω) ^{Note}
900	TBD	TBD

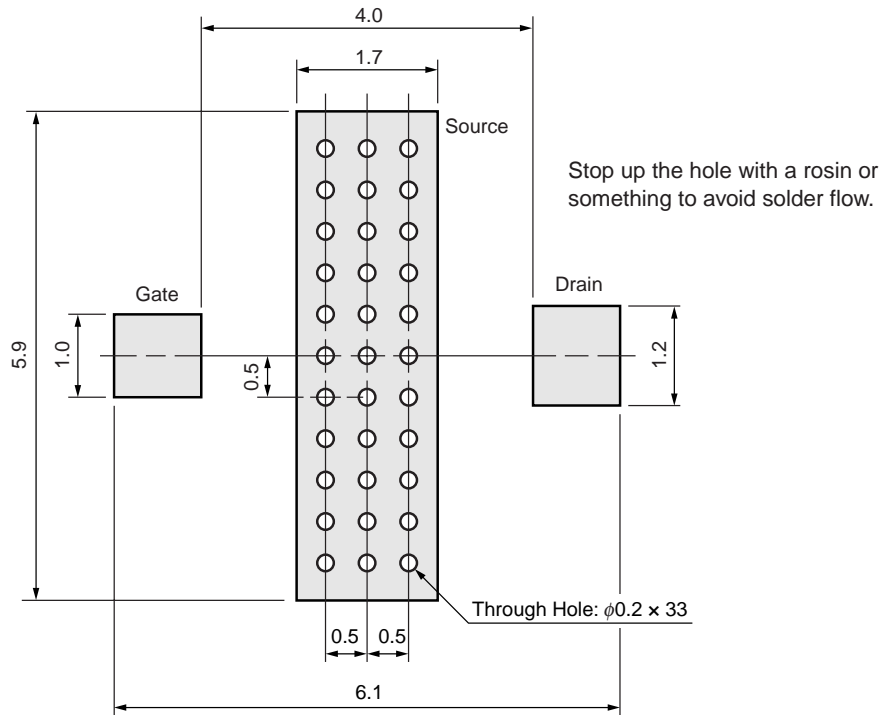
Note Z_{OL} is the conjugate of optimum load impedance at given voltage, idling current, input power and frequency.

★ PACKAGE DIMENSIONS

79A (UNIT: mm)



79A PACKAGE RECOMMENDED P.C.B. LAYOUT (UNIT: mm)



RECOMMENDED SOLDERING CONDITIONS

This product should be soldered and mounted under the following recommended conditions. For soldering methods and conditions other than those recommended below, contact your nearby sales office.

Soldering Method	Soldering Conditions	Condition Symbol
Infrared Reflow	Peak temperature (package surface temperature) : 260°C or below Time at peak temperature : 10 seconds or less Time at temperature of 220°C or higher : 60 seconds or less Preheating time at 120 to 180°C : 120±30 seconds Maximum number of reflow processes : 3 times Maximum chlorine content of rosin flux (% mass) : 0.2%(Wt.) or below	IR260
VPS	Peak temperature (package surface temperature) : 215°C or below Time at temperature of 200°C or higher : 25 to 40 seconds Preheating time at 120 to 150°C : 30 to 60 seconds Maximum number of reflow processes : 3 times Maximum chlorine content of rosin flux (% mass) : 0.2%(Wt.) or below	VP215
Wave Soldering	Peak temperature (molten solder temperature) : 260°C or below Time at peak temperature : 10 seconds or less Preheating temperature (package surface temperature) : 120°C or below Maximum number of flow processes : 1 time Maximum chlorine content of rosin flux (% mass) : 0.2%(Wt.) or below	WS260
Partial Heating	Peak temperature (pin temperature) : 350°C or below Soldering time (per pin of device) : 3 seconds or less Maximum chlorine content of rosin flux (% mass) : 0.2%(Wt.) or below	HS350-P3

Caution Do not use different soldering methods together (except for partial heating).

- **The information in this document is current as of July, 2003. The information is subject to change without notice. For actual design-in, refer to the latest publications of NEC's data sheets or data books, etc., for the most up-to-date specifications of NEC semiconductor products. Not all products and/or types are available in every country. Please check with an NEC sales representative for availability and additional information.**
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